TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT process) (Bias Resistor built-in Transistor)

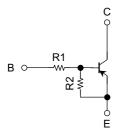
RN2967FE, RN2968FE, RN2969FE

Switching, Inverter Circuit, Interface Circuit and Driver Circuit Applications.

- Two devices are incorporated into an Extreme-Super-Mini (6 pin) package.
- Incorporating a bias resistor into a transistor reduces parts count.
 Reducing the parts count enable the manufacture of ever more compact equipment and save assembly cost.
- Complementary to RN1967FE~RN1969FE

Equivalent Circuit and Bias Resistor Values

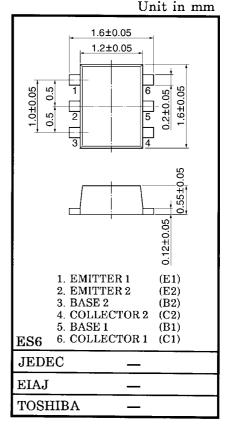
Maximum Ratings (Ta = 25°C) (Q1, Q2 common)



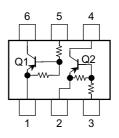
Type No.	R1 (kΩ)	R2 (kΩ)
RN2967FE	10	47
RN2968FE	22	47
RN2969FE	47	22

Characteristics		Symbol	Rating	Unit	
Collector-base voltage		V_{CBO}	-50	V	
Collector-emitter voltage		V_{CEO}	-50	V	
	RN2967FE		-6	V	
Emitter-base voltage	RN2968FE	V_{EBO}	-7		
	RN2969FE		-15		
Collector current		Ic	-100	mA	
Collector power dissipation		P _C (Note)	100	mW	
Junction temperature		Tj	150	°C	
Storage temperature range		T _{stg}	−55~150	°C	

Note: Total rating



Equivalent Circuit (top view)



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Electrical Characteristics (Ta = 25°C) (Q1, Q2 common)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	RN2967FE~2969FE	I _{CBO}	$V_{CB} = -50 \text{ V}, I_E = 0$	_	_	-100	nA
		I _{CEO}	$V_{CE} = -50 \text{ V}, I_B = 0$	_	_	-500	IIA
	RN2967FE	I _{EBO}	$V_{EB} = -6 \text{ V}, I_C = 0$	-0.081	_	-0.15	mA
Emitter cut-off current	RN2968FE		$V_{EB} = -7 \text{ V}, I_{C} = 0$	-0.078	_	-0.145	
	RN2969FE		$V_{EB} = -15 \text{ V}, I_{C} = 0$	-0.167	_	-0.311	
	RN2967FE	h _{FE}	$V_{CE} = -5 \text{ V},$ $I_{C} = -10 \text{ mA}$	80	_	_	
DC current gain	RN2968FE			80	_	_	
	RN2969FE			70	_	_	
Collector-emitter saturation voltage	RN2967FE~2969FE	V _{CE} (sat)	$I_C = -5 \text{ mA},$ $I_B = -0.25 \text{ mA}$	_	-0.1	-0.3	V
Input voltage (ON)	RN2967FE	V _{I (ON)}	V _{CE} = -0.2 V, I _C = -5 mA	-0.7	_	-1.8	V
	RN2968FE			-1.0	_	-2.6	
	RN2969FE			-2.2	_	-5.8	
Input voltage (OFF)	RN2967FE	V _{I (OFF)}	V _{CE} = -5 V, I _C = -0.1 mA	-0.5	_	-1.0	V
	RN2968FE			-0.6	_	-1.16	
	RN2969FE			-1.5	_	-2.6	
Transition frequency	RN2967FE~2969FE	f _T	$V_{CE} = -10 \text{ V},$ $I_{C} = -5 \text{ mA}$	_	200	_	MHz
Collector output capacitance	RN2967FE~2969FE	C _{ob}	$V_{CB} = -10 \text{ V}, I_E = 0,$ f = 1 MHz	_	3	6	pF
Input resistor	RN2967FE	R1	_	7	10	13	kΩ
	RN2968FE			15.4	22	28.6	
	RN2969FE			32.9	47	61.1	
Resistor ratio	RN2967FE	R1/R2	_	0.191	0.2	0.232	
	RN2968FE			0.421	0.468	0.515	
	RN2969FE			1.92	2.14	2.35	

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[•] The information contained herein is subject to change without notice.

Type Name	Marking
RN2967FE	Type name Y Y H
RN2968FE	Type name
RN2969FE	Type name Y Y J